

isc Silicon NPN Power Transistor

BD539D

DESCRIPTION

- DC Current Gain -
- : $h_{FE} = 40(Min.)@I_{C} = 0.5A$
- · Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO}= 120V(Min)
- Complement to Type BD540D
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

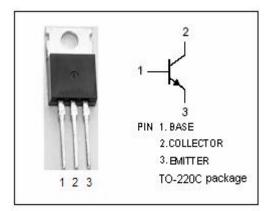
 Designed for use in medium power linear and switching applications.

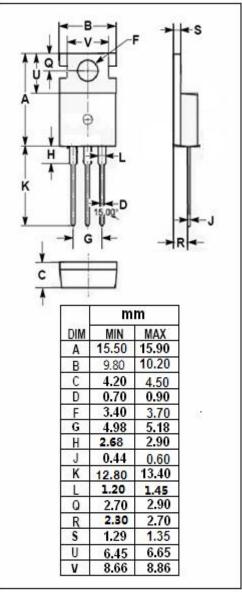
ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{CBO}	Collector-Base Voltage	120	V	
VCEO	Collector-Emitter Voltage		V	
V _{EBO}	Emitter-Base Voltage 5		V	
Ic	Collector Current-Continuous 5		Α	
P _C	Collector Power Dissipation @ T _a =25°C	2	W	
	Collector Power Dissipation @ Tc=25°C	45		
TJ	Junction Temperature 150		$^{\circ}$	
T _{stg}	Storage Temperature Range -65		$^{\circ}$	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth j-c	Thermal Resistance, Junction to Case	2.78	°C/W
R _{th j-a}	R _{th j-a} Thermal Resistance, Junction to Ambient		°C/W







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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 30mA; I _B = 0	120		V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 1A; I _B = 0.125A		0.25	٧
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 3A; I _B = 0.375A		0.8	٧
V _{CE(sat)-3}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 1A		1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 3A; V _{CE} = 4V		1.25	V
I _{CEO}	Collector Cutoff Current	V _{CB} = 90V; I _B = 0		0.3	mA
Ices	Collector Cutoff Current	V _{CE} = 120V; V _{BE} = 0		0.2	mA
ІЕВО	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0		1.0	mA
h _{FE-1}	DC Current Gain	I _C = 0.5A; V _{CE} = 4V	40		
h _{FE-2}	DC Current Gain	I _C = 1A; V _{CE} = 4V	30		
h _{FE-3}	DC Current Gain	I _C = 3A; V _{CE} = 4V	12		

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